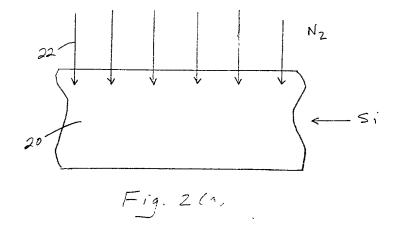
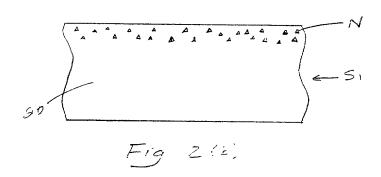
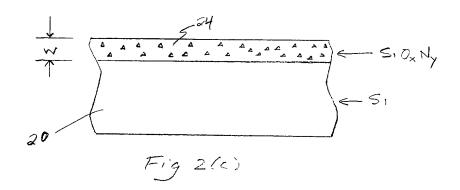
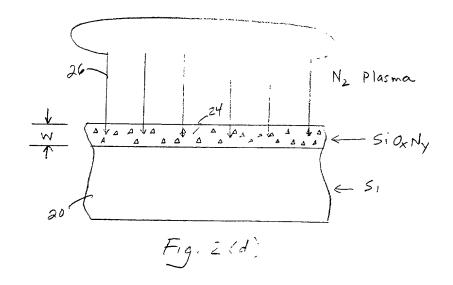


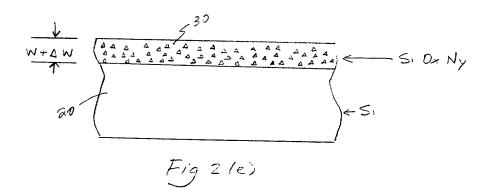
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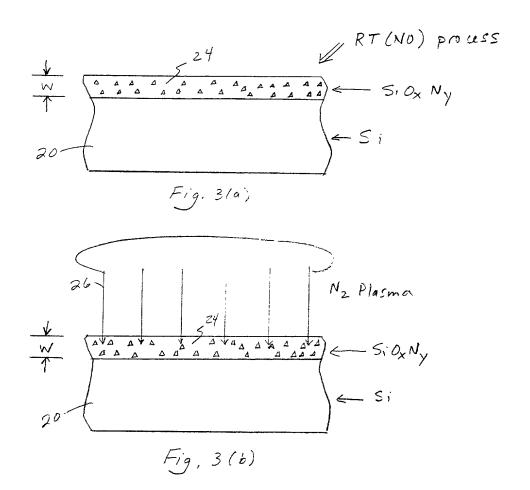


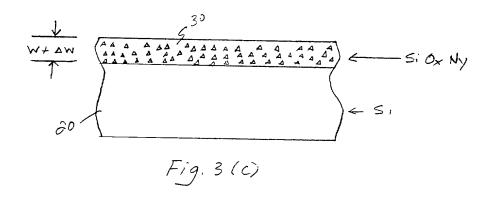












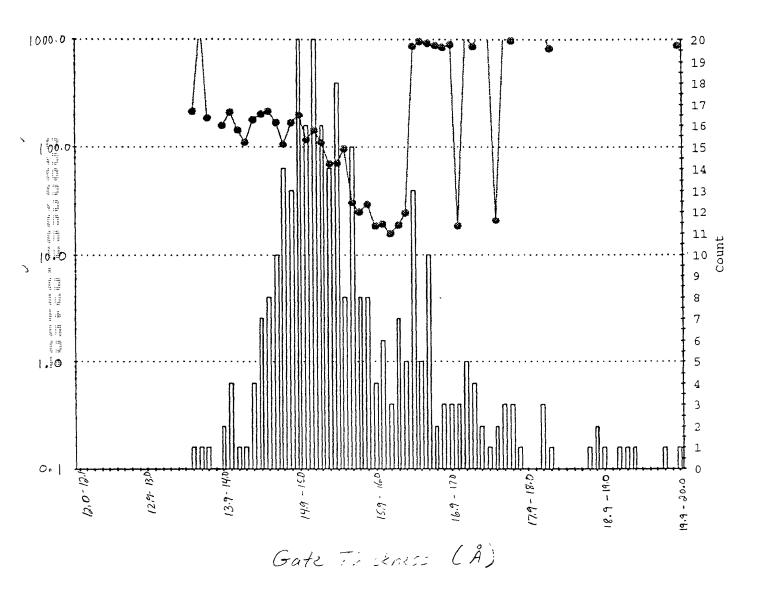
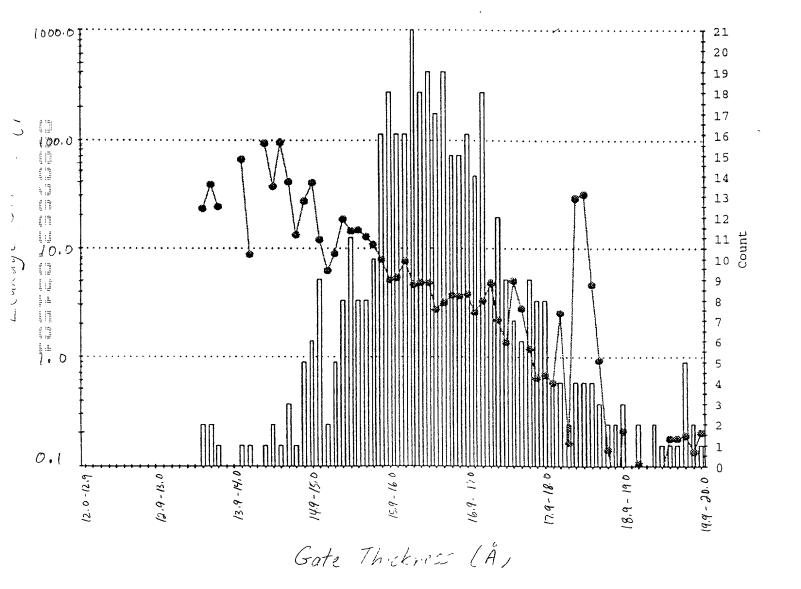


Fig. 4

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5:02 + RPN (Prior Art.



F13.5

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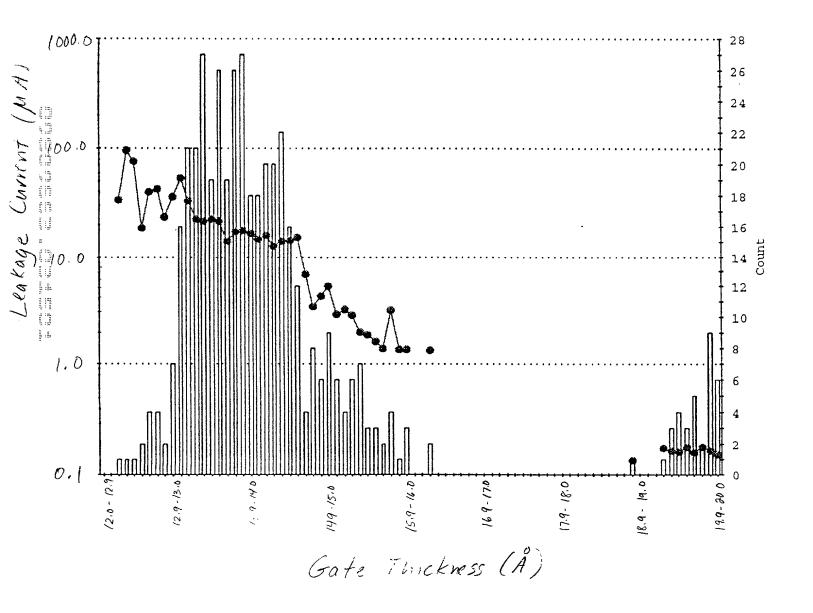


Fig. 6

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Uniformity of Gate Film

	Mean Thickness (mm)	
RPN of SiOz (Dry)	1.74	0.287
RPN of SiO2 (Wet)	1.68	0.115
RTNO	1.70	0.0293
RTNO + RPN @ 550°C	1.74	0.0246
RTNO + RPV@ 750°C	1.73	0.0296

Fig. 7

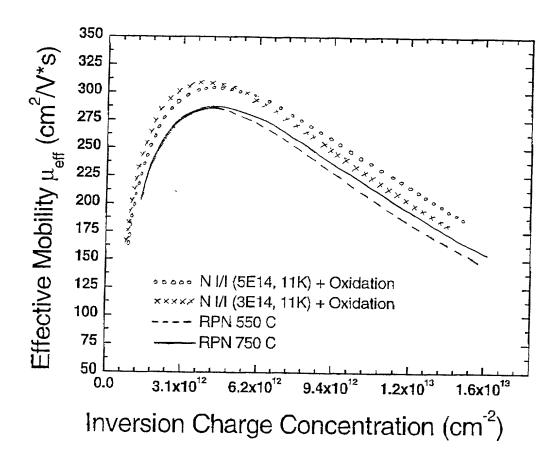


Figure 8